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United States Patent Application Publication

20250266299

Kind Code

A1

Publication Date

August 21, 2025

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SEMICONDUCTOR DEVICE HAVING A DUMMY SECTION AND METHOD FOR MANUFACTURING THE SAME

Abstract

A semiconductor device includes a semiconductor substrate, active elements, first insulating film, an electrode pad, a second insulating film, a ring-shaped dummy portion, island-shaped dummy portions, and a Through Silicon VIA electrode. The semiconductor substrate has an obverse surface, which is divided into an active area and an element-absence area surrounding the active area, and a reverse surface. The ring-shaped dummy portion and the island-shaped dummy portions are disposed in the element-absence area. The ring-shaped dummy portion and each of the island-shaped dummy portions have top surfaces coplanar with a top surface of the second insulating film, and a maximum distance of an outer edge of the ring-shaped dummy portion to a closest point on the inner edge of the ring-shaped dummy portion in a plan view is larger than a width of each of the island-shaped dummy portions in the plan view.

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Appl. No.: 19/203167

Filed: May 09, 2025

Foreign Application Priority Data

JP 2008-180289 Jul. 10, 2008

Related U.S. Application Data

parent US continuation 18360814 20230728 parent-grant-document US 12300543 child US 19203167

parent US continuation 17117727 20201210 parent-grant-document US 11798847 child US 18360814
parent US division 16460969 20190702 parent-grant-document US 10892189 child US 17117727
parent US division 15879006 20180124 ABANDONED child US 16460969
parent US division 12458324 20090708 parent-grant-document US 9892968 child US 15879006

Publication Classification

Int. Cl.: **H01L21/768** (20060101); **H01L21/3105** (20060101); **H01L21/321** (20060101);
H01L21/762 (20060101); **H01L23/48** (20060101); **H10F39/00** (20250101)

U.S. Cl.:

CPC **H01L21/76898** (20130101); **H01L21/76224** (20130101); **H01L21/76819** (20130101);
H01L23/481 (20130101); H01L21/31053 (20130101); H01L21/3212 (20130101);
H01L21/76229 (20130101); H01L2224/02372 (20130101); H01L2224/0401 (20130101);
H01L2224/05 (20130101); H01L2224/05548 (20130101); H01L2224/13021 (20130101);
H01L2224/13024 (20130101); H01L2225/06541 (20130101); H10F39/811 (20250101)

Background/Summary

CROSS-REFERENCE TO RELATED APPLICATION [0001] This application is a continuation application of and claims the priority benefit of U.S. application Ser. No. 18/360,814, filed on Jul. 28, 2023, which is a continuation application of and claims the priority benefit of U.S. application Ser. No. 17/117,727, filed on Dec. 10, 2020 (issued on Oct. 24, 2023, as U.S. Pat. No. 11,798,847), which is a divisional application of and claims the priority benefit of U.S. application Ser. No. 16/460,969, filed on Jul. 2, 2019 (issued on Jan. 12, 2021, as U.S. Pat. No. 10,892,189), which is a divisional application of and claims the priority benefit of U.S. application Ser. No. 15/879,006, filed on Jan. 24, 2018, which is a divisional application of and claims the priority benefit of U.S. application Ser. No. 12/458,324, filed on Jul. 8, 2009 (issued on Feb. 13, 2018, as U.S. Pat. No. 9,892,968). Furthermore, these applications claim the benefit of priority of Japanese Patent Application No. 2008-180289, filed on Jul. 10, 2008. The entire disclosures of these prior U.S. and Japanese applications are incorporated herein by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

[0002] The present invention relates to a method for manufacturing a semiconductor device and a semiconductor package, and particularly relates to a semiconductor device having a Through Silicon VIA electrode structure.

2. Description of the Related Art

[0003] Recent versions of information devices such as digital cameras and mobile phones equipped with a camera function embody considerably higher levels of miniaturization, density, and functionality. A wafer-level chip size package (hereinafter referred to as W-CSP) is a known technique for reducing the size of CCD sensors, CMOS sensors, and other imaging elements used in such devices to fit in a chip-scale package.

[0004] The W-CSP is a new concept package in which all the assembly steps are completed in a wafer state.

[0005] A Through Silicon VIA electrode structure is adopted in the image sensor of a W-CSP structure because reliability can be improved and the device can be made smaller. An electrode that

allows the semiconductor device to have signal interchange with the exterior is ordinarily formed on the same surface as the formation surface of the semiconductor elements. In contrast, with Through Silicon VIA electrodes, Through Silicon VIA holes are formed in the thickness direction of the chip from the reverse side of the chip using microfabrication, conductive wiring is formed inside the Through Silicon VIA holes, and the conductive wiring is connected to surface electrodes, whereby signal interchange is made possible from the reverse surface of the chip which is not ordinarily used. Stacking a plurality of chips using a Through Silicon VIA electrode technique and forming signal transmission pathways in the thickness direction of the chip makes it possible to make wiring distances shorter than with conventional wiring. Therefore, packaging density can be dramatically improved and speed and reliability can be increased. Methods for manufacturing CSP having a Through Silicon VIA electrode are described in, e.g., Japanese Laid-open Patent Application Nos. 2006-128171 and 2005-235858.

[0006] A CMOS sensor, for example, is an imaging element for reading an electric charge accumulated in a photodiode that has been converted to voltage and amplified in each pixel, and is provided with a photodiode, a cell amplifier, and the like inside a unit cell. A CMOS sensor is composed of a plurality of active elements that constitute a photodiode and a cell amplifier on a semiconductor substrate, and STI (shallow trench isolation) is used for discrete insulation between each active element. The region for forming transistors, diodes, and other active elements on the semiconductor substrate is referred to as an active area, while a region other than the active area is referred to as a non-active area. In other words, STI and other element isolation regions belong to the non-active area. Flattening by CM P (chemical mechanical polishing) is carried out in the step for forming an STI on the semiconductor substrate, and dishing occurs. In dishing, the center portion of the STI is formed into a concave dish-shape by the difference in polishing rates between the oxide film constituting the STI and the nitride film provided as a stopper during polishing when the surface area of the STI region is increased. Difficulties arise in later steps because the flatness of the substrate is detracted when dishing occurs. A technique for preventing dishing involves the formation of a dummy pattern having a plurality of island-shaped dummy sections inside the non-active area, which is the location when dishing occurs. The dummy pattern is formed by leaving the base material of the silicon substrate in island shapes inside the STI region, and is therefore referred to as a dummy active. Dishing can be prevented because the difference between the polishing rates in the CMP step is lessened by the uniform formation of a dummy active in the non-active area (STI region).

[0007] In an image sensor having a W-CSP structure, a Through Silicon VIA electrode is generally formed in the non-active area in which active elements are not formed, and a plurality of dummy actives is formed in order to prevent dishing in the non-active area as described above. In other words, a dry etching step for forming Through Silicon VIA holes in the non-active area in which the plurality of dummy actives is formed is included in the steps for manufacturing an image sensor. However, there is a problem in that notches (outwardly expanding depressions in the side wall of the Through Silicon VIA hole) are generated in the sidewall of the Through Silicon VIA holes when Through Silicon VIA holes are formed so as to pass through the non-active area in which the plurality of dummy actives are uniformly disposed.

[0008] FIG. 1A is a plan view showing the surface structure of a semiconductor substrate in the Through Silicon VIA electrode formation area in a conventional image sensor. The Through Silicon VIA hole **21** has a substantially cylindrical shape and is formed in the non-active area **100** in which photodiodes, transistors and other active elements are not formed. The non-active area **100** comprises an STI region mainly composed of SiO₂. A plurality of island-shaped dummy actives **200** for preventing dishing is uniformly disposed in the non-active area (STI region). The Through Silicon VIA hole **21** is formed so as to pass through the non-active area in which the plurality of dummy actives **200** is arrayed. At this point, dummy actives **200** are present in positions in which the outer edge of the Through Silicon VIA hole **21** passes because the array pitch and the

dimensions of the dummy actives **200** are relatively small in comparison with the size of the Through Silicon VIA hole **21**.

[0009] FIG. **1B** is a cross-sectional view along the line **1B-1B** in FIG. **1A**. An interlayer insulating film **12** is formed on the semiconductor substrate **10**. The electrode pad **13** electrically connected to the sensor section is formed in the interlayer insulating film **12**. The Through Silicon VIA electrode is formed by forming a Through Silicon VIA hole **21** from the reverse surface of the semiconductor substrate toward the electrode pad **13** by dry etching. Notches **300** are generated in the dry etching process when dummy actives **200** are present in positions through which the outer edge of the Through Silicon VIA hole passes, i.e., when the outer edge of the Through Silicon VIA hole intersects with the dummy actives **200**. The notches **300** are depressions formed in the sidewall of the Through Silicon VIA hole **21** in positions at the depth near the boundary between the interlayer insulating film **12** and the semiconductor substrate **10**. In FIG. **1A**, the locations where notches are generated are indicated by shading. It is apparent from the drawing that the notches **300** are generated only in locations where the outer edge of the Through Silicon VIA hole **21** intersects with the dummy actives **200**.

[0010] In the step for forming a Through Silicon VIA electrode, a Through Silicon VIA hole **21** is formed, after which a process is carried out to sequentially form plating composed of a barrier metal, a plating seed layer, and electroconductive wiring of the Through Silicon VIA electrode on the inner wall of the Through Silicon VIA hole. Cu is generally used as the plating. However, because Cu is a typical material that constitutes metal contamination in the silicon device and diffuses into the silicon substrate and the interlayer insulating film at lower temperatures, there is a risk of a deterioration of the device performance and reliability, for example, junction leaks and dielectric breakdowns in the interlayer insulating film. For this reason, a barrier metal composed of Ti, Ti/Ni, or the like is formed between the semiconductor substrate and the Cu film that constitutes the electroconductive wiring of the Through Silicon VIA electrode in order to prevent Cu-diffusion into the silicon substrate.

[0011] However, it is difficult to form a sufficient barrier metal in the area where notches are generated in the case that notches occur in the sidewall of the Through Silicon VIA hole, and insufficient coverage by the barrier metal is liable to occur in notched area. In this case, Cu could diffuse into the semiconductor substrate in the areas where there is insufficient coverage by the barrier metal, and the device performance and reliability are seriously affected.

SUMMARY OF THE INVENTION

[0012] The present invention has been contrived in view of the above-described issues, and an object is to provide a semiconductor device having a non-active area in which a dummy pattern is formed on the semiconductor substrate and a Through Silicon VIA electrode is formed so as to pass through the non-active area, wherein the quality, reliability, and stability of the semiconductor device is improved by preventing the occurrence of notches that are generated in a side wall of the Through Silicon VIA electrode.

[0013] The semiconductor device of the present invention is a semiconductor device that comprises a semiconductor substrate having an active area in which a plurality of active elements are formed, and a non-active area excepting the active area; at least one electrode pad electrically connected to any of the active elements; and at least one Through Silicon VIA electrode electrically connected to the electrode pad by way of the non-active area, wherein the non-active area has an insulating region obtained by forming an insulating film on the semiconductor substrate, and a dummy section obtained by leaving a base material of the semiconductor substrate in the insulating region, and an outer edge of the Through Silicon VIA electrode does not intersect with the boundary between the insulating region and the dummy section.

[0014] The method for manufacturing a semiconductor device of the present invention is method for manufacturing a semiconductor device that comprises a step for forming, on a semiconductor substrate, an active area in which a plurality of active elements are formed, and a non-active area

excepting the active area; a step for forming at least one electrode pad electrically connected to any of the active elements; and a step for forming at least one Through Silicon VIA electrode electrically connected to the electrode pad by way of the non-active area, wherein the step for forming the non-active area includes a step for forming a dummy section obtained by leaving a base material of the semiconductor substrate in an insulating region composed of an insulating film; and the Through Silicon VIA electrode is formed such that an outer edge of thereof does not intersect with the boundary between the insulating region and the dummy section.

[0015] The method for manufacturing a semiconductor package of the present invention is a method for manufacturing a semiconductor package that includes the semiconductor device described above, comprising a step for forming a Through Silicon VIA hole from the reverse surface of the semiconductor substrate to the electrode pad in a Through Silicon VIA electrode formation area of said semiconductor substrate; a step for forming an insulating film on an inner wall of the Through Silicon VIA hole and the reverse surface of the semiconductor substrate; a step for selectively removing the insulating film of the bottom surface of the Through Silicon VIA hole and exposing the electrode pad inside the Through Silicon VIA hole; a step for sequentially forming a barrier metal and an electroconductive film for covering the reverse surface of the semiconductor substrate and the inner wall of the Through Silicon VIA hole to form the Through Silicon VIA electrode and reverse surface wiring electrically connected to said Through Silicon VIA electrode on the reverse surface of the semiconductor substrate; a step for forming an insulating film having an aperture on the reverse surface of the semiconductor substrate; and a step for forming an external terminal on the exposed portion of the reverse surface wiring through the aperture.

[0016] In accordance with the semiconductor device and the method for manufacturing a semiconductor device of the present invention, dishing of the STI region can be prevented by a dummy pattern formed in the non-active area. The Through Silicon VIA electrode formation area of the non-active area has a dummy pattern formed so that no area is generated wherein the outer edge of the Through Silicon VIA electrode intersects the dummy section. Therefore, etching ions are not scattered in the vicinity of the sidewall of the Through Silicon VIA hole and the occurrence of notches in the sidewall of the Through Silicon VIA hole can be prevented. Accordingly, a barrier metal can be formed on the sidewall of the Through Silicon VIA hole without the occurrence of insufficient coverage, and the diffusion of Cu constituting the plating as well as other impurities into the semiconductor substrate can be reliably prevented.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0017] FIG. 1A is a plan view showing the configuration of a conventional dummy pattern formed in a non-active area.

[0018] FIG. 1B is a cross-sectional view along the line 1B-1B in FIG. 1A.

[0019] FIG. 2 is a cross-sectional view of an image sensor according to an embodiment of the present invention.

[0020] FIG. 3 is a plan view showing the configuration of the reverse surface of the image sensor according to an embodiment of the present invention.

[0021] FIG. 4A is a plan view showing the configuration of the dummy pattern in the Through Silicon VIA electrode formation area according to an embodiment of the present invention.

[0022] FIG. 4B is a cross-sectional view along the line 4B-4B in FIG. 4A.

[0023] FIG. 5 is a plan view showing the configuration of the dummy pattern in the Through Silicon VIA electrode formation area according to another embodiment of the present invention.

[0024] FIG. 6 is a plan view showing the configuration of the dummy pattern in the Through

Silicon VIA electrode formation area according to another embodiment of the present invention. [0025] FIG. 7 is a plan view showing the configuration of the dummy pattern in the Through Silicon VIA electrode formation area according to another embodiment of the present invention. [0026] FIG. 8 is a plan view showing the configuration of the dummy pattern in the Through Silicon VIA electrode formation area according to another embodiment of the present invention. [0027] FIGS. 9A to 9G are cross-sectional views showing the steps for manufacturing an image sensor according to an embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

[0028] The supposed mechanism by which notches are generated in the side wall of a Through Silicon VIA hole when a Through Silicon VIA electrode is formed through a non-active area in which a plurality of dummy actives are uniformly disposed will be described with reference to FIGS. 1A and 1B before a description regarding embodiments of the present invention is given.

[0029] Notches in the sidewall of a Through Silicon VIA hole are known to be generated in the dry etching step of a semiconductor substrate when a Through Silicon VIA hole is formed. In the dry etching step, an STI region **11** composed of SiO₂ is not etched by selective etching in the step for etching silicon as the base material of a semiconductor substrate **10**. For this reason, the inventor posits that etching ions emitted by an etching device are reflected in the STI region **11**, are scattered in the lateral direction, and collide with the sidewall of the Through Silicon VIA hole **21**, whereby the sidewall of the Through Silicon VIA hole is etched and notches **300** are generated. In other words, it is thought that when a boundary between the STI region and the dummy actives **200** is present in the vicinity of the sidewall of the Through Silicon VIA hole **21**, etching ions scattered at the boundary collide in a high-energy state with the sidewall of the Through Silicon VIA hole and form notches.

[0030] Embodiments of the present invention described below are improvements on the configuration of a dummy pattern of a non-active area in the Through Silicon VIA electrode formation area, in that a dummy pattern is provided in such a way as to avoid the formation of an area in which the outer edge of the Through Silicon VIA hole intersects the boundary between the dummy section and the STI region. Therefore, a boundary between the dummy section and the STI region, which causes the etching ions to be scattered, is not formed in the vicinity of the sidewall of the Through Silicon VIA hole. Embodiments of the present invention are described below with reference to the drawings.

[0031] FIG. 2 is a cross-sectional view of an image sensor according to an embodiment of the present invention. A semiconductor substrate **10** composed of a single-crystal silicon or the like constitutes the main body of the image sensor, and formed on the substrate are transistors and other active elements **30** constituting a photodiode and peripheral circuits for processing signals that have undergone photoelectric exchange in the photodiode. Light receiving elements are formed on the semiconductor substrate **10** in a number commensurate with the number of pixels, and the light emitted from an imaging target is formed as an image on the surface of the light receiving elements by externally provided lenses or another optical system. Each of the light receiving elements outputs a photoelectric conversion signal that corresponds to the intensity of the received light, as a detected output signal. Image data is generated from the position of each light receiving element and the detected output signals.

[0032] An interlayer insulating film **12** composed of SiO₂ or the like is formed on the surface of the semiconductor substrate **10**. Electroconductive wiring **14** having a multilayer structure electrically connected to the active elements **30** is formed inside the interlayer insulating film **12**. An electrode pad **13** that is electrically connected to the electroconductive wiring **14** is provided in the region further outside the region in which the active elements **30** constituting the sensor section are formed. A color filter **15** for separating the received light into three primary colors is provided on the surface of the interlayer insulating film **12**. A cover glass **17** is mounted on the interlayer insulating film **12** via an adhesive sheet **16**.

[0033] A Through Silicon VIA electrode **20** is provided in the semiconductor substrate **10**, from the reverse surface of the semiconductor substrate to the electrode pad **13** inside the interlayer insulating film **12**. The Through Silicon VIA electrode **20** is formed by sequentially forming on the bottom surface and sidewall of the Through Silicon VIA hole a barrier metal **22** composed of Ti, Ti/Ni, or the like, a plating seed film **23** composed of Cu or the like and, and a plating film **24** composed of Cu or the like. These electroconductive films constituting the Through Silicon VIA electrode **20** are connected to the electrode pad **13** on the bottom surface of the Through Silicon VIA hole, and are connected to the reverse surface wiring **25** that extends to the reverse surface of the semiconductor substrate **10**. The insulation between electroconductive film of the Through Silicon VIA electrode **20** or reverse surface wiring **25** and the semiconductor substrate **10** is ensured by the insulating film **18** composed of SiO₂ or the like formed along the sidewall of the Through Silicon VIA hole and the reverse surface of the semiconductor substrate **10**. A solder resist **40** is formed on the reverse surface of the semiconductor substrate **10** so as to embed the Through Silicon VIA hole of the Through Silicon VIA electrode **20**. An aperture is formed in the solder resist **40**. A reverse surface electrode pad that constitutes a portion of the reverse surface wiring **25** is provided in the exposed portion through the aperture. A solder bump **41** is provided on the reverse surface electrode pad, thereby constituting an external connection terminal electrically connected to the electrode pad **13** via the Through Silicon VIA electrode **20** and the reverse surface wiring **25**. In this manner, the package of the image sensor of the present embodiment has a W-CSP configuration, which is the same size as the semiconductor substrate **10**.

[0034] FIG. **3** is a plan view of the image sensor of the present embodiment as seen from the reverse surface side of the semiconductor substrate **10**. In the drawing, a plurality of Through Silicon VIA electrodes **20** is formed along the outer edge of the semiconductor substrate **10**. The solder bumps **41** are arranged in the form of a grid on the reverse surface of the semiconductor substrate **10** and are electrically connected to the corresponding Through Silicon VIA electrodes **20** via the reverse surface wiring **25**. The region enclosed by the broken line in the drawing is a region for forming a sensor circuit in which photodiodes, transistors, and other active elements are formed. Each of the Through Silicon VIA electrodes **20** is formed in areas that correspond to the non-active area in which active elements are not formed.

[0035] FIG. **4A** is a plan view showing the surface structure of the semiconductor substrate **10** in the formation area of the Through Silicon VIA electrode **20**. The formation area of the Through Silicon VIA electrode **20** is clearly shown in the drawing. The Through Silicon VIA hole **21** of the Through Silicon VIA electrode having a substantially cylindrical shape is formed in the non-active area **100** in which photodiodes and other active elements are not formed. The STI region **11** formed by embedding SiO₂ film in a trench formed in the surface of the semiconductor substrate **10** extends across the entire surface of the non-active area **100**. Since the STI region **11** formed in the non-active area **100** has a relatively large surface area, there is a concern that dishing will occur in the CMP step that is carried out when the STI region **11** is formed. Therefore, a dummy pattern is formed in the non-active area **100** in order to prevent dishing. The dummy pattern is provided by disposing a plurality of island-shaped dummy actives **200** in the non-active area **100**. The dummy actives **200** are formed by partially exposing the silicon in the SiO₂ film constituting the STI region. Therefore, active elements can be formed on the dummy actives, and since the dummy actives are formed exclusively for the purpose of preventing dishing and do not contribute any function to the image sensor, transistors and other active elements do not need to be formed on the dummy actives. However, in the present invention, active elements may be formed on the dummy actives. In other words, a gate electrode and drain and source regions may be formed on the dummy actives, but these will not contribute function to the image sensor and electrodes and regions having functionality as a dummy pattern are essentially included in the dummy actives. In this case, the active elements formed on the dummy actives must be isolated from the main circuit so that they do not operate.

[0036] In the present embodiment, the dummy actives **200** are not formed in the region that overlaps the Through Silicon VIA electrode **20**. In other words, the dummy actives **200** are formed only in the region outside the Through Silicon VIA electrode formation area and are not formed inside the Through Silicon VIA electrode formation area.

[0037] FIG. **4B** is a cross-sectional view along the line **4B-4B** in FIG. **4A**. As described above, the dummy actives **200** are not present inside the Through Silicon VIA electrode formation area, the Through Silicon VIA hole **21** is formed in the region in which only the SiO₂ film constituting the STI region **11** is present, and there is no portion in which the outer edge of the Through Silicon VIA electrode **20** intersects with the boundary between the STI region and the dummy actives. Therefore, the boundary between the STI region and the dummy actives where etching ions are scattered is not present in the vicinity of the sidewall of the Through Silicon VIA hole **21**. The lateral scattering of the etching ions can be completely prevented in the dry etching step for forming the Through Silicon VIA hole **21**. Therefore, the generation of notches in the sidewall of the Through Silicon VIA hole **21** can be effectively prevented. Since the barrier metal **22** can be formed without the occurrence of insufficient coverage on the sidewall of the Through Silicon VIA hole **21**, the diffusion of Cu constituting the plating film **24** into the semiconductor substrate can be prevented.

[0038] FIG. **5** is a plan view showing the surface structure of the semiconductor substrate **10** in the Through Silicon VIA electrode formation area of the semiconductor device according to a second embodiment of the present invention. The formation area of the Through Silicon VIA electrode **20** is clearly shown in the drawing. In the present embodiment, dummy actives are not formed in the region that overlaps the Through Silicon VIA electrode formation area in the same manner as the first embodiment described above. In the present embodiment, a rectangular ring-shaped dummy active **201** that surrounds the Through Silicon VIA electrode formation area is additionally provided. In other words, a formation area for the Through Silicon VIA electrode **20** is arranged in an STI region **11** extending inside of the rectangular ring-shaped dummy active **201** wherein dummy actives are not formed. The STI region **11** in which a plurality of island-shaped dummy actives **200** are uniformly disposed extends around the periphery of the rectangular ring-shaped dummy active **201**. There is no portion in which the outer edge of the Through Silicon VIA electrode **20** intersects with the boundary between the STI region and the dummy actives even in the case that the non-active area **100** in the Through Silicon VIA electrode formation area has such a structure. In the same manner as the first embodiment, the lateral scattering of etching ions can be completely prevented in the dry etching step for forming the Through Silicon VIA hole **21**. Accordingly, the generation of notches in the sidewall of the Through Silicon VIA hole **21** can be effectively prevented. Since the barrier metal **22** can be formed without the occurrence of insufficient coverage on the sidewall of the Through Silicon VIA hole **21**, the diffusion of Cu constituting the plating film **24** into the semiconductor substrate can be prevented. In the present embodiment, the anti-dishing effect can be improved by providing a rectangular ring-shaped dummy active **201** around the outer periphery of the Through Silicon VIA electrode formation area. In other words, since dummy actives are not disposed in the Through Silicon VIA electrode formation area, the surface area of the portion composed only of the STI region is increased, resulting in a structure that is liable to undergo dishing in the portion. However, the effect of preventing dishing is greater than that of the first embodiment because the density of the dummy actives is increased at the periphery of the Through Silicon VIA electrode formation area by surrounding the Through Silicon VIA electrode formation area with the rectangular ring-shaped dummy active **201**. The external shape of the rectangular ring-shaped dummy active **201** is not limited to a rectangular shape, and, e.g., a polygonal shape other than a quadrangular shape, a circular shape, or any shape that follows the outer edge of the Through Silicon VIA hole **21** may be used.

[0039] FIG. **6** is a plan view showing the surface structure of the semiconductor substrate **10** in the

Through Silicon VIA electrode formation area of the semiconductor device according to a third embodiment of the present invention. The formation area of the Through Silicon VIA electrode **20** is clearly shown in the drawing. As shown in the drawing, a plurality of island-shaped dummy actives **202** are formed in the Through Silicon VIA electrode formation area in the present embodiment, which is different from the first embodiment (FIG. **4A**) described above. Dummy actives are not arranged in a position through which the outer edge of the Through Silicon VIA hole **21** passes. Dummy actives are disposed in the regions outside and in the center of the Through Silicon VIA electrode formation area. In view of the fact that notches occur only in portions in which the outer edge of the Through Silicon VIA hole **21** pass through dummy actives, as shown in FIG. **1A**, it is thought that there is substantially no effect of scattered etching ions when the dummy actives are not disposed on the outer edge of the Through Silicon VIA hole **21**. Therefore, dummy actives **202** can be formed inside of the Through Silicon VIA electrode formation area in a range that is not affected by laterally scattered etching ions. There are no portions in which the outer edge of the Through Silicon VIA electrode **20** intersects with the boundary between the STI region and the dummy actives even in the case that the non-active area **100** in the Through Silicon VIA electrode formation area has such a structure. On the other hand, dummy actives **202** are present in the Through Silicon VIA electrode formation area, and because of this, etching ions are scattered in the boundary between the STI region and the dummy actives **202**. However, since an adequate distance to the sidewall of the Through Silicon VIA hole **21** is assured, it is expected that a possibility that the scattered etching ions etch the sidewalls of the Through Silicon VIA hole **21** and notches are generated lowers. Therefore, the diffusion of Cu constituting the plating film into the semiconductor substrate can be prevented because the barrier metal can be formed without the occurrence of insufficient coverage on the sidewall of the Through Silicon VIA hole **21**. The effect of preventing dishing is greater than that of the first embodiment described above because the density of the dummy actives around the periphery of the Through Silicon VIA electrode formation area is made greater by providing dummy actives **202** inside of the Through Silicon VIA electrode formation area.

[0040] FIG. **7** is a plan view showing the surface structure of the semiconductor substrate **10** in the Through Silicon VIA electrode formation area of the semiconductor device according to a fourth embodiment of the present invention. The formation area of the Through Silicon VIA hole **21** is clearly shown in the drawing. As shown in the drawing, a rectangular dummy active **203** having a larger surface area than the surface area of the aperture of the Through Silicon VIA hole **21** is disposed in the Through Silicon VIA electrode formation area. The STI region **11** in which a plurality of island-shaped dummy actives **200** are uniformly disposed extends around the periphery of the rectangular dummy active **203**. There are no portions in which the outer edge of the Through Silicon VIA electrode **20** intersects with the boundary between the STI region and the dummy actives even in the case that the non-active area **100** in the Through Silicon VIA electrode formation area has such a structure. Therefore, the lateral scattering of etching ions can be completely prevented in the dry etching step for forming the Through Silicon VIA hole **21**.

Accordingly, the generation of notches in the sidewall of the Through Silicon VIA hole **21** can be effectively prevented. Since the barrier metal can be formed without the occurrence of insufficient coverage on the sidewall of the Through Silicon VIA hole **21**, the diffusion of Cu constituting the plating film **24** into the semiconductor substrate can be prevented. The effect of preventing dishing is greater than that of the first embodiment described above because the density of the dummy actives around the periphery of the Through Silicon VIA electrode formation area is made greater by providing a dummy active **203** having a relatively large surface area in the Through Silicon VIA electrode formation area. In the present embodiment the external shape of the dummy active **203** is rectangular, but no limitation is imposed thereby, and other polygonal shapes, a circular shape, or any shape that follows the outer edge of the Through Silicon VIA hole **21** may be used.

[0041] FIG. **8** is a plan view showing the surface structure of the semiconductor substrate **10** in the

Through Silicon VIA electrode formation area of the semiconductor device according to a fifth embodiment of the present invention. The formation area of the Through Silicon VIA electrode is clearly shown in the drawing. A rectangular ring-shaped dummy active **204** is formed so as to surround an STI region **11 b** provided inside the Through Silicon VIA electrode formation area and so as to occupy a region having a fixed range that includes the outer edge of the Through Silicon VIA electrode **20**. A plurality of island-shaped dummy actives **205** is disposed in the STI region **11 b**. The STI region **11** in which a plurality of island-shaped dummy actives **200** is uniformly disposed extends around the periphery of the rectangular ring-shaped dummy active **204**. There is no portion in which the outer edge of the Through Silicon VIA electrode **20** intersects with the boundary between the STI region and the dummy actives even in the case that the non-active area **100** in the Through Silicon VIA electrode formation area has such a structure. Provided that an adequate distance from the boundary between the dummy active **204** and the STI region **11 b** to the sidewall of the Through Silicon VIA hole **21** is assured, then even when etching ions are scattered in the boundary, there is little possibility that notches will be generated when the scattered etching ions etch the sidewalls of the Through Silicon VIA hole **21**. Therefore, the diffusion of the plating film into the semiconductor substrate can reliably be prevented because the barrier metal can be formed without the occurrence of insufficient coverage on the sidewall of the Through Silicon VIA hole **21**. The effect of preventing dishing is greater than that of the first embodiment described above because the density of the dummy actives around the periphery of the Through Silicon VIA electrode formation area is made greater by providing dummy actives **204** and **205** in the Through Silicon VIA electrode formation area.

[0042] Described next with reference to FIGS. **9A** to **9G** is a method for manufacturing a package of an image sensor using a semiconductor device having the structure described in the embodiments above.

[0043] First, a wafer is prepared having a semiconductor substrate **10** on which are formed active elements **30** composed of photodiodes, cell amplifiers, and other sensor sections, color filters **15**, electrode pads **13**, and the like. A dummy pattern having a configuration shown in the embodiments described above is formed (FIG. **9A**) in the non-active area including the Through Silicon VIA electrode formation area of the semiconductor substrate **10**.

[0044] Meanwhile, a cover glass **17** is prepared in which a protective film **19** has been affixed to the surface. The protective film **19** is provided for protecting the cover glass **17** from damage during the manufacturing steps and is affixed so as to cover the entire upper surface of the cover glass **17**. The cover glass **17** is then affixed to the light receiving elements formation surface of the semiconductor substrate **10** via an adhesive sheet **16** (FIG. **9B**).

[0045] Next, the reverse surface of the semiconductor substrate **10** is polished until the thickness of the semiconductor substrate **10** reaches a predetermined value (FIG. **9C**).

[0046] A photoresist having an aperture in the portion that corresponds to the Through Silicon VIA electrode formation area is subsequently formed on the reverse surface of the semiconductor substrate **10**. The semiconductor substrate **10** exposed through the aperture of the photoresist is dry-etched from the reverse surface side to form a Through Silicon VIA hole **21** that reaches the electrode pad **13** inside the interlayer insulating film **12** (FIG. **9D**). The Through Silicon VIA hole **21** is formed in the non-active area in which the dummy pattern corresponding to the embodiments described above is formed. In other words, the boundary between the dummy actives and the STI region is not present in the vicinity of the sidewall of the Through Silicon VIA hole **21** and etching ions are not scattered in the lateral direction. Therefore, notches are not generated in the sidewall of the Through Silicon VIA hole **21**.

[0047] Next, an insulating film **18** composed of SiO₂ film is deposited by CVD method so as to cover the reverse surface of the semiconductor substrate **10** and the inner wall of the Through Silicon VIA hole **21**. The insulating film **18** deposited on the bottom surface of the Through Silicon VIA hole **21** is etched to expose the electrode pad **13** inside the Through Silicon VIA hole **21**.

(FIG. 9E).

[0048] Next, a barrier metal **22** composed of Ti, Ti/Ni, or the like and a plating seed film **23** composed of Cu are sequentially formed on the sidewall and bottom surface of the Through Silicon VIA hole **21** as well as the reverse surface of the semiconductor substrate **10** by sputtering method. Because notches have not been generated in the sidewall of the Through Silicon VIA hole **21**, the barrier metal can therefore be formed without the occurrence of insufficient coverage. Next, an electrode is connected to the plating seed film **23** and a plating film **24** composed of Cu is formed on the inner wall of the Through Silicon VIA hole **21** by electroplating method, thereby forming a Through Silicon VIA electrode **20**. Reverse surface wiring **25** is then formed on the reverse surface of the semiconductor substrate **10**. A resist is thereafter formed on the reverse surface of the semiconductor substrate **10** on which Cu film is formed using a photosensitive dry film or the like. The reverse surface wiring **25** is formed by etching Cu film through the resist. The Through Silicon VIA electrode **20** is electrically connected to the electrode pad **13** on the bottom surface of the Through Silicon VIA hole **21**. The reverse surface wiring **25** is electrically connected to the electrode pad **13** via the Through Silicon VIA electrode **20** (FIG. 9F).

[0049] Next, a solder resist **40** as an insulating film composed of a photosetting epoxy resin is coated so as to cover the entire reverse surface of the semiconductor substrate **10** on which the reverse surface wiring **25** is formed. The solder resist **40** is dehydrated and then the exposed portions of the solder resist **40** through a photoresist are photo-cured. The interior of the Through Silicon VIA hole **21** is filled with the solder resist **40**. Unexposed portions of the solder resist **40** are selectively removed to form apertures in the solder bump formation region. Next, a solder bump **41** is formed in the pad area of the reverse surface wiring **25** exposed through the aperture of the solder resist **40** by electroplating method or the like (FIG. 9G).

[0050] Next, the protective film **19** affixed to the cover glass **17** is peeled away, the cover glass is affixed to a wafer tape, and an image sensor is formed into a chip shape through the dicing process. The image sensor package is completed by carrying out the steps described above.

[0051] According to the semiconductor device and the method for manufacturing a semiconductor device of the present invention, it is obvious from the description above that dishing in the STI region can be prevented by using a dummy pattern formed in the non-active area. Dummy actives are disposed in the Through Silicon VIA electrode formation area of the non-active area such that there are no portions in which the outer edge of the Through Silicon VIA electrode intersects with the dummy actives; i.e., there are no portions in which the STI region and the dummy actives are adjacent in the vicinity of the sidewall of the Through Silicon VIA hole. Therefore, etching ions are not scattered in the vicinity of the sidewall of the Through Silicon VIA hole, and the occurrence of notches in the sidewall of the Through Silicon VIA hole can be prevented. A barrier metal can be formed on the sidewall of the Through Silicon VIA hole without the occurrence of insufficient coverage, and the diffusion of Cu and other impurities constituting the plating film into the semiconductor substrate can be reliably prevented.

[0052] The present invention has been described above with reference to the preferred embodiments. It is apparent that various modifications and changes can be envisioned by persons skilled in the art. All such modifications and changes are understood to be included within the range of the appended claims.

Claims

1. A semiconductor device comprising: a semiconductor substrate having an obverse surface and a reverse surface opposite to the obverse surface, wherein the obverse surface is divided into an active area and an element-absence area surrounding the active area; a plurality of active elements disposed on the obverse surface within the active area; a first insulating film formed over the obverse surface of the semiconductor substrate; an electrode pad embedded in the first insulating

film and is electrically connected to the active elements; a second insulating film disposed in the element-absence area, wherein the second insulating film is sandwiched between the obverse surface of the semiconductor substrate and the first insulating film; a ring-shaped dummy portion disposed in the element-absence area; a plurality of island-shaped dummy portions disposed in the element-absence area, wherein the ring-shaped dummy portion and each of the island-shaped dummy portions have top surfaces coplanar with a top surface of the second insulating film, and a maximum distance of an outer edge of the ring-shaped dummy portion to a closest point on the inner edge of the ring-shaped dummy portion in a plan view is larger than a width of each of the island-shaped dummy portions in the plan view; and a Through Silicon VIA electrode penetrating through the semiconductor substrate and the ring-shaped dummy portion to be in physical contact with the electrode pad.

2. The semiconductor device of claim 1, wherein the ring-shaped dummy portion has a distance across being larger than that of each of the island-shaped dummy portions.

3. The semiconductor device of claim 1, wherein a distance between two adjacent island-shaped dummy portions in the plan view is smaller than a diameter of the Through Silicon VIA electrode.

4. The semiconductor device of claim 1, wherein the island-shaped dummy portions are arranged in a staggered manner.

5. The semiconductor device of claim 1, wherein the second insulating film surrounds the outer edge of the ring-shaped dummy portion from the plan view.

6. The semiconductor device of claim 1, wherein the outer edge of the ring-shaped dummy portion is rectangular from the plan view.

7. A semiconductor device comprising: a semiconductor substrate having an obverse surface and a reverse surface opposite to the obverse surface, wherein the obverse surface is divided into an active area and an element-absence area surrounding the active area; a plurality of active elements disposed on the obverse surface within the active area, wherein the element-absence area is free of any of the active elements; a first insulating film formed over the obverse surface of the semiconductor substrate, wherein the first insulating film extends across the element-absence area and the active area; an electrode pad which is provided inside the first insulating film and is electrically connected to the active elements; a ring-shaped dummy portion disposed in the element-absence area; a plurality of island-shaped dummy portions disposed in the element-absence area, wherein the island-shaped dummy portions are arranged on two opposite sides of the ring-shaped dummy portion in a plan view, and a maximum distance of an outer edge of the ring-shaped dummy portion to a closet point on an inner edge of the ring-shaped dummy portion in the plan view is larger than a width of each of the island-shaped dummy portions in the plan view; and a Through Silicon VIA electrode penetrating through the semiconductor substrate from the reverse surface of the semiconductor substrate to the obverse surface.

8. The semiconductor device of claim 7, wherein the ring-shaped dummy portion has a distance across being larger than that of each of the island-shaped dummy portions.

9. The semiconductor device of claim 7, wherein a distance between two adjacent island-shaped dummy portions in the plan view is smaller than a diameter of the Through Silicon VIA electrode.

10. The semiconductor device of claim 7, wherein the island-shaped dummy portions are arranged in columns, and each of the island-shaped dummy portions from two adjacent columns are misaligned along a horizontal direction from the plan view.

11. The semiconductor device of claim 10, wherein the island-shaped dummy portions are further arranged in rows, and each of the island-shaped dummy portions from two adjacent rows are misaligned along a vertical direction from the plan view.

12. The semiconductor device of claim 7, wherein the inner edge of the ring-shaped dummy portion is circular from the plan view, and the outer edge of the ring-shaped dummy portion is rectangular from the plan view.

13. The semiconductor device of claim 7, wherein each of the island-shaped dummy portions is

rectangular from the plan view.

14. A method for manufacturing a semiconductor device, comprising: providing a semiconductor substrate having an obverse surface and a reverse surface opposite to the obverse surface; forming an insulating film on the obverse surface; forming a plurality of island-shaped dummy portions and a ring-shaped dummy portion on the obverse surface, wherein the ring-shaped dummy portion and each of the island-shaped dummy portions have top surfaces coplanar with a top surface of the insulating film, a first set of the island-shaped dummy portions is formed inside of an inner edge of the ring-shaped dummy portion, and a second set of the island-shaped dummy portions is formed outside of an outer edge of the ring-shaped dummy portion; forming an interlayer insulating film on the ring-shaped dummy portion, the island-shaped dummy portions, and the insulating film; forming an electrode pad so as to be buried inside the interlayer insulating film; removing a portion of the semiconductor substrate, a portion of the insulating film, a portion of the ring-shaped dummy portion, a portion of the interlayer insulating film, and the first set of the island-shaped dummy portions to form a Through Silicon VIA hole extending from the reverse surface of the semiconductor substrate to the electrode pad, wherein the Through Silicon VIA hole exposes the electrode pad; and forming a Through Silicon VIA electrode in the Through Silicon VIA hole, wherein the Through Silicon VIA electrode is in physical contact with the electrode pad.

15. The method for manufacturing the semiconductor device of claim 14, wherein the Through Silicon VIA hole has a first aperture part on the electrode pad and a second aperture part on the reverse surface of the semiconductor substrate, and the second aperture part is larger than the first aperture part.

16. The method for manufacturing the semiconductor device of claim 15, wherein the first aperture part is circular.

17. The method for manufacturing the semiconductor device of claim 14, wherein the first set of the island-shaped dummy portions formed inside of the inner edge of the ring-shaped dummy portion are arranged in an array.

18. The method for manufacturing the semiconductor device of claim 14, wherein the insulating film covers the outer edge of the ring-shaped dummy portion.

19. The method for manufacturing the semiconductor device of claim 14, wherein the ring-shaped dummy portion is a rectangular ring-shaped dummy portion.

20. The method for manufacturing the semiconductor device of claim 14, wherein each of the island-shaped dummy portions is rectangular from a plan view.
